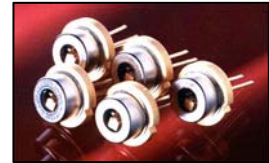




RLT9820G

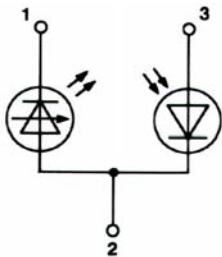
TECHNICAL DATA



High Power Infrared Laserdiode

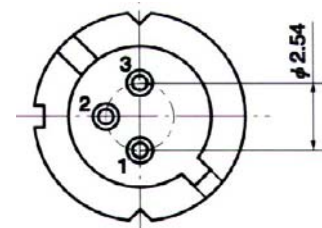
Structure: **GaAlAs double heterostructure**
 Lasing wavelength: **980 nm typ.**
 Max. optical power: **20 mW, multimode**
 Package: **9 mm**

NOTE!
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:

- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	25	mW
LD Reverse Voltage	V _{R(LD)}	1.5	V
PD Reverse Voltage	V _{R(PD)}	6	V
Operating Temperature	T _C	-10 .. +50	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw		20		mW
Threshold Current	I _{th}	cw		25	30	mA
Operation Current	I _{op}	P _o = 20 mW	60	75	100	mA
Lasing Aperture	A			1x15		µm ²
Lasing Wavelength	λ _p	P _o = 20 mW	970	980	990	nm
Beam Divergence	θ	P _o = 20 mW		20	25	°
Beam Divergence	θ _⊥	P _o = 20 mW		45	50	°
Differential Efficiency	dP _o /dI _{op}	P _o = 20 mW	0.4	0.7	1.0	mW/mA
Monitor Current	I _m	P _o = 20 mW	150	350	1200	µA